

REMARKS

By this Preliminary Amendment new claims 101-109 have been added. A reading of new claims 101-109 on the drawings and specification is as follows.

101. (new) A method for fabricating a semiconductor component **(10-Figure 3V)** comprising:

providing a base die **(12-Figure 3A)**;

forming a conductive via **(26-Figure 3K)** in the base die **(12-Figure 3K)**;

forming a metal layer **(87-Figure 3K)** on the conductive via **(26-Figure 3K)**;

providing a secondary die **(14-Figure 3O)** comprising a contact **(24-Figure 3O)**; and

bonding the contact **(24-Figure 3P)** on the secondary die to the metal layer **(87-Figure 3P)** on the conductive via.

(antecedent basis for the bonding step at page 25, lines 37 to page 26, line 2 of the specification)

102. (new) The method of claim 101 wherein the layer comprises a metal selected from the group consisting of nickel, zinc, chromium, palladium and gold.

(antecedent basis at page 15, lines 18-22 of the specification)

103. (new) The method of claim 101 wherein the layer comprises nickel.

(antecedent basis at page 15, lines 18-22 of the specification)

104. (new) The method of claim 101 further comprising thinning the base die **(12)** prior to the bonding step.

(antecedent basis at page 21, lines 34-38 of the specification)

105. (new) The method of claim 101 wherein the secondary die **(14)** comprises a thinned die.

(antecedent basis at page 3, lines 28-31 of the specification)

106. (new) The method of claim 101 wherein the base die **(12-Figure 3)** has a larger peripheral outline than the secondary die **(14-Figure 2)**.

107. (new) A method for fabricating a semiconductor component **(10-Figure 3V)** comprising:

providing a base die **(12-Figure 3A)**;

forming a plurality of conductive vias **(26-Figure 3K)** in the base die, each conductive via comprising a conductive material in an opening and a metal layer **(87-Figure 3K)** on the conductive material;

providing a secondary die **(14-Figure 30)** comprising a plurality of contacts **(24-Figure 30)**;

bonding the contacts **(24-Figure 30)** on the secondary die to the conductive vias **(26-Figure 3K)** on the base die; and

forming a plurality of terminal contacts **(18-Figure 3U)** on the base die in electrical communication with the conductive vias.

108. (new) The method of claim 107 wherein the conductive material comprises solder and the metal layer comprises nickel.

(antecedent basis for solder at page 24, line 21, antecedent basis for nickel at page 15, lines 18-22)

109. (new) The method of claim 107 further comprising thinning the base die and the secondary die prior to the bonding step.

(antecedent basis at page 21, lines 34-38 of the specification)

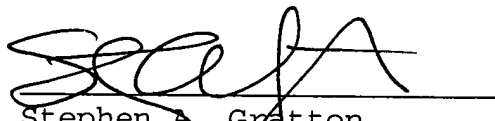
Conclusion

In addition to the new claims, the "Cross Reference To Related Applications" has been amended to include a patent number for the issued parent case. Also being submitted with this Preliminary Amendment is an Information Disclosure Statement with the issued parent case.

Favorable consideration and allowance of original claims 51-79 and new claims 101-109 is requested. Should any issues arise that will advance this case to allowance, the Examiner is asked to contact the undersigned by telephone.

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